

Dual P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)						
	0.116 at V _{GS} = - 4.5 V	- 4.5 ^a							
- 20	0.155 at V _{GS} = - 2.5 V	- 4.5 ^a	4.9 nC						
	0.205 at V _{GS} = - 1.8 V	- 4.5 ^a							

FEATURES

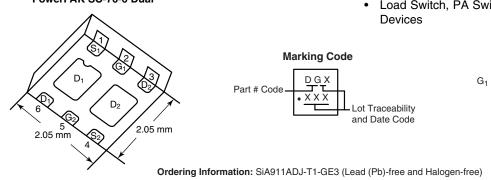
- · Halogen-free
- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance

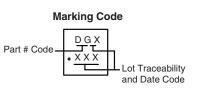
APPLICATIONS

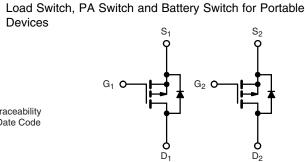
Devices



PowerPAK SC-70-6 Dual







P-Channel MOSFET P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise no	ted	
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 20	V
Gate-Source Voltage		V_{GS}	± 8	v
	T _C = 25 °C		- 4.5 ^a	
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	I _D	- 4.5 ^a	
Continuous Brain Current (1) = 130 C)	T _A = 25 °C	טי	- 3.2 ^{b, c}	
	T _A = 70 °C		- 2.6 ^{b, c}	A
Pulsed Drain Current		I _{DM}		
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	- 4.5 ^a	
Continuous Cource-Drain Diode Current	T _A = 25 °C	'5	- 1.5 ^{b, c}	
	T _C = 25 °C		6.5	
Maximum Power Dissipation	T _C = 70 °C	P _D	4.2	□ w
Maximum Fower Dissipation	T _A = 25 °C	ט י	1.8 ^{b, c}	
	T _A = 70 °C		1.1 ^{b, c}	
Operating Junction and Storage Temperature Ra	nge	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature	a) ^{d, e}		260	

THERMAL RESISTANCE RATINGS								
Parameter		Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R_{thJA}	55	70	°C/W			
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	15	19	O/ VV			

Notes:

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 110 °C/W.

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SPECIFICATIONS T _J = 25 °C, unless otherwise noted									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static	1 1/	V 0.V.I. 050 A		1	I				
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, } I_D = -250 \mu\text{A}$	- 20			V			
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 19		mV/°C			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	<u> </u>		2.4					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	- 0.4		- 1	V			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA			
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μΑ			
Zoro date Voltage Brain Garront	1033	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 10	μι			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le 5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 8			Α			
		$V_{GS} = -4.5 \text{ V}, I_D = -2.8 \text{ A}$		0.096	0.116				
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -2.3 \text{ A}$		0.126	0.155	Ω			
		V _{GS} = - 1.8 V, I _D = - 0.54 A		0.165	0.205				
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 2.8 A		7		S			
Dynamic ^b	•			1	'				
Input Capacitance	C _{iss}			345					
Output Capacitance	C _{oss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		65		pF			
Reverse Transfer Capacitance	C _{rss}			50					
· · · · · · · · · · · · · · · · · · ·		V _{DS} = - 10 V, V _{GS} = - 8 V, I _D = - 3.5 A		8.4	13	nC			
Total Gate Charge	Q_g	2.5		4.9	7.4				
Gate-Source Charge	Q _{gs}	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 3.5 A		0.75					
Gate-Drain Charge	Q _{gd}			1.2					
Gate Resistance	R _q	f = 1 MHz		6		Ω			
Turn-On Delay Time	t _{d(on)}			15	25				
Rise Time	t _r	$V_{DD} = -10 \text{ V, R}_{1} = 2.85 \Omega$		45	70	- -			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -3.5 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		20	30				
Fall Time	t _f	Ç		10	15				
Turn-On Delay Time	t _{d(on)}			5	10	ns			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 2.85 Ω		10	15	1			
Turn-Off Delay Time	t _{d(off)}	054.77		20	30	=			
Fall Time	t _f	g		10	15	-			
Drain-Source Body Diode Characterist									
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 4.5				
Pulse Diode Forward Current	I _{SM}				- 8	Α			
Body Diode Voltage	V _{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.8	- 1.2	V			
Body Diode Reverse Recovery Time	t _{rr}			30	60	ns			
Body Diode Reverse Recovery Charge	Q _{rr}			20	40	nC			
Reverse Recovery Fall Time	t _a	$I_F = -4.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		15		ns			
Reverse Recovery Rise Time	t _b			15					
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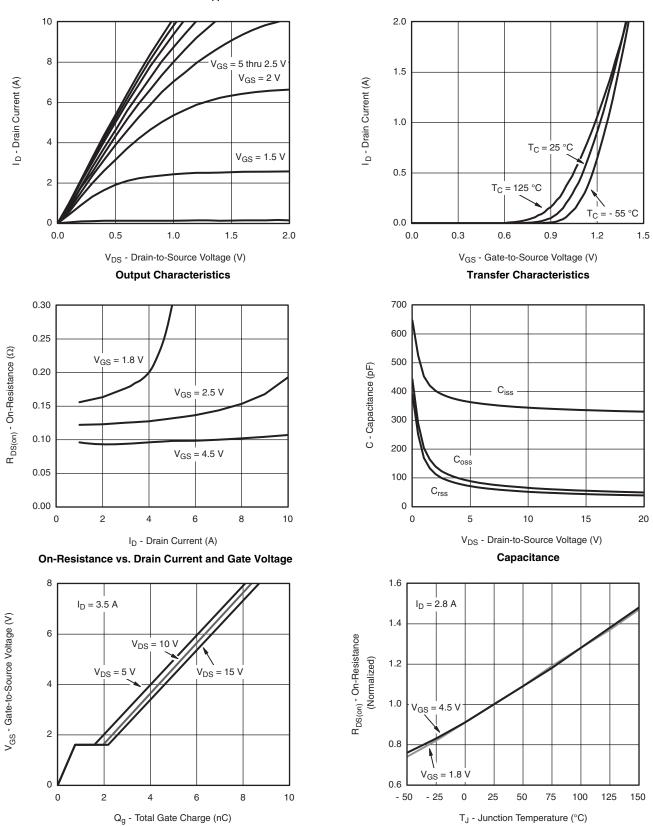
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted

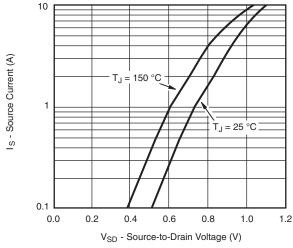


Gate Charge

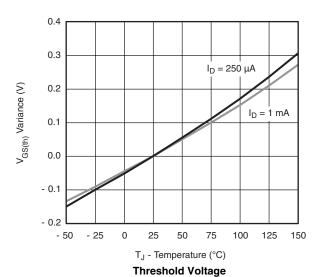
On-Resistance vs. Junction Temperature

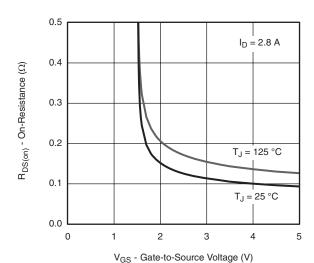
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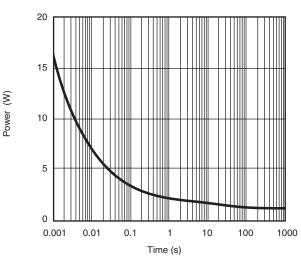


Soure-Drain Diode Forward Voltage

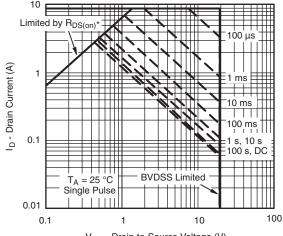




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



V_{DS} - Drain-to-Source Voltage (V)

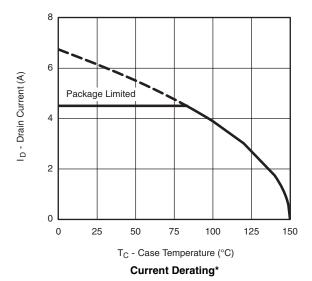
Safe Operating Area, Junction-to-Case

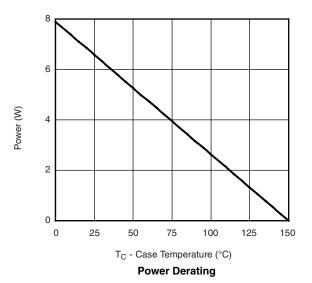
^{*} V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified





TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted

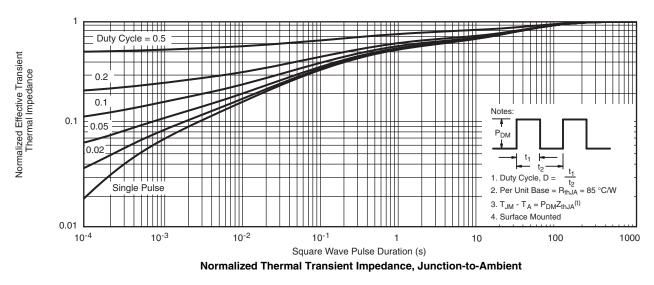


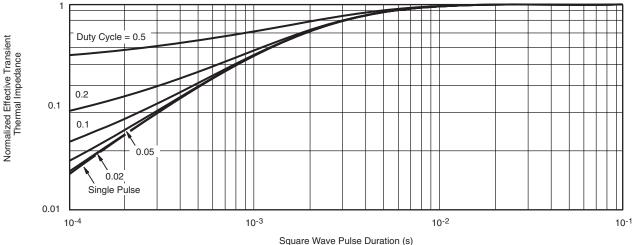


^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

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TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted





Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see https://www.vishay.com/ppg?68968.





PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

		SINGLE PAD						DUAL PAD				
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP			0.011 TYP		0.275 TYP			0.011 TYP		
K1		0.400 TYP		0.016 TYP		0.320 TYP			0.013 TYP			
K2		0.240 TYP		0.009 TYP		0.252 TYP		0.010 TYP				
К3		0.225 TYP		0.009 TYP					•	•		
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

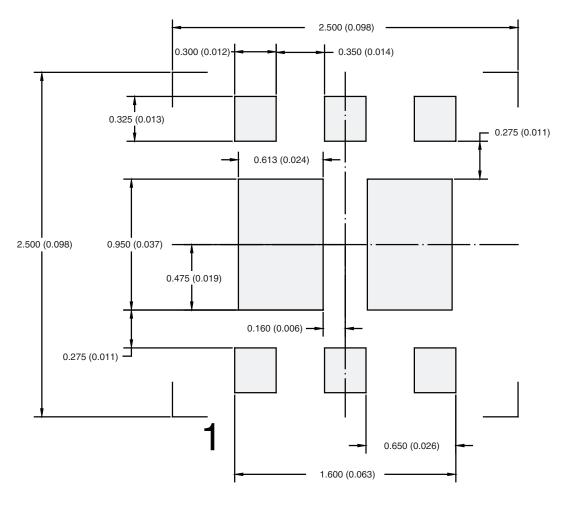
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

Return to Index



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